

APPLICATION OF LOW ENERGY ION
IMPLANTATION TO THE CREATION OF
CONTACTS TO ULTRATHIN FILMS

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S u m m a r y

The results of experimental researches of the creation of ohmic contacts on the surface of natural ultrathin films ($\approx 1000 \text{ \AA}$) of Si/CoSi_2 by using the implantation of Ba ions are given. Preliminary implantation of Ba^+ ions allows us to take reliable ohmic contacts on ultrathin films of silicon. We revealed that silicides of Ba have low specific resistance ($\rho \approx 20 \div 30 \mu\Omega \cdot \text{sm}$).